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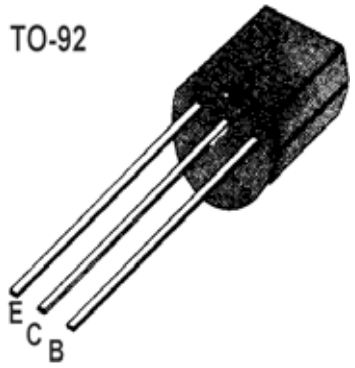
S8550 (ECB) PNP EPITAXIAL SILICON TRANSISTOR

1W OUTPUT AMPLIFIER OF PORTABLE
RADIOS IN CLASS
B PUSH-PULL OPERATION

* Complimentary to **S8050**
* Collector Current Icm =0.8A
* Collector Dissipation:Pc=0.8W(Tc=25 ℃)

ABSOLUTE MAXIMUM RATINGS(T_A=25 ℃)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-25	V
Emitter -Base Voltage	V_{EBO}	-6	V
Collector Current	I_C	-0.8	A
Collector Dissipation	P_C	0.8	W
Junction Temperature	T_J	150	℃
Storage Temperature	T_{STG}	-65 ~150	℃



ELECTRICAL CHARACTERISTICS (T_A=25 ℃)

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV_{CBO}	I_C= -100μA,I_E=0	-40			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	I_C= -2mA,I_B=0	-25			V
Emitter-Base Breakdown Voltage	BV_{EBO}	I_E= -100μA,I_C=0	-6			V
Collector Cut-off Current	I_{CBO}	V_{CB}= -35V,I_E=0			-100	nA
Emitter Cut-off Current	I_{EBO}	V_{EB}= -6V,I_C=0			-100	nA
DC Current Gain	H_{FE1}	V_{CE}= -1V,I_C= -5mA	45	170		
	H_{FE2}	V_{CE}= -1V,I_C= -500mA	85	160	300	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C= -500mA,I_B= -50mA		-0.28	-0.5	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	I_C= -500mA,I_B= -50mA		-0.98	-1.2	V
Base-Emitter Voltage	V_{BE}	V_{CE}= -1V,I_C= -10mA		-0.66	-1.0	V
Output Capacitance	C_{OB} F=1MHz	V_{CB}= -10V,I_E= 0		15		pF
Current Gain-Bandwidth Product	f_T	V_{CE}= -10V,I_C= -50mA	100	200		MHz

H_{FE}(2) CLASSIFICATIC

Classification	B	C	D	E	F
H_{FE}(2)	85-160	120-200	160-300	300-400	400-500